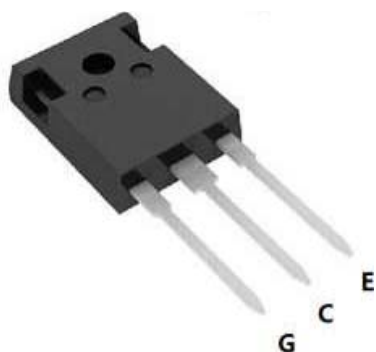




IGBT Modules

V_{CE}	650	V
I_C	30	A
$V_{CE(SAT)} I_C=30A$	2.00	V

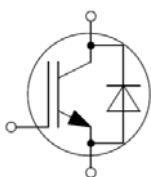
Applications

- High frequency switching application
- Medical applications
- Uninterruptible power supply
- Motion/servo control

Features

- Low switching losses
- Maximum junction temperature 175°C
- Positive temperature coefficient
- High ruggedness, temperature stable
- High short circuit capability(5us)
- Isolated heatsink using DBC technology

Circuit



Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter Breakdown Voltage	V_{CE}	650	V
DC Collector Current, limited by T_{jmax} $T_C=25^{\circ}C$ $T_C=100^{\circ}C$	I_C	60 30	A
Diode Forward Current, limited by T_{jmax} $T_C=25^{\circ}C$ $T_C=100^{\circ}C$	I_F	30 15	A
Continuous Gate-Emitter Voltage	V_{GE}	± 20	V
Transient Gate-Emitter Voltage	V_{GE}	± 30	V
Turn off Safe Operating Area $V_{CE} \leq 1200V$, $T_j \leq 150^{\circ}C$		120	A
Pulsed Collector Current, $V_{GE}=15V$, t_p limited by T_{jmax}	I_{CM}	120	A
Diode Pulsed Current, t_p limited by T_{jmax}	I_{Fpuls}	120	A
Short Circuit Withstand Time, $V_{GE}=15V$, $V_{CC}=900V$, $V_{CEM} \leq 1200V$	T_{sc}	5	μs
Power Dissipation, $T_j=25^{\circ}C$	P_{tot}	187	W



Operating Junction Temperature	T_j	-40...+175	°C
Storage Temperature	T_s	-55...+150	°C
Soldering Temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	°C

Electrical Characteristics of the IGBT ($T_j = 25^\circ\text{C}$ unless otherwise specified):

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Collector-Emitter Breakdown Voltage	BV_{CES}	$V_{GE}=0V, I_C=250\mu A$	650		-	V
Gate Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=250\mu A$	4.5	5.0	5.5	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=30A$ $T_j=25^\circ\text{C}$, $T_j=125^\circ\text{C}$ $T_j=150^\circ\text{C}$		2.00 2.30 2.40	2.40	V
Zero Gate Voltage Collector Current	I_{CES}	$V_{CE}=650V, V_{GE}=0V$ $T_j=25^\circ\text{C}$, $T_j=150^\circ\text{C}$			1 5	mA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE}=0V, V_{GE}=\pm 20V$			100	nA

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic						
Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V$, $f=1\text{MHz}$	-	1.60	-	nF
Reverse Transfer Capacitance	C_{res}		-	0.09	-	
Gate Charge	Q_G	$V_{CC}=300V, I_C=30A, V_{GE}=15V$	-	0.15	-	uC
Short Circuit Collector Current	I_{SC}	$V_{GE}=15V, t_{sc}\leq 5\mu s$, $V_{CC}=300V, T_j\leq 150^\circ\text{C}$	-	150	-	A



Electrical Characteristics of the Diode (T_J= 25°C unless otherwise specified):

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Diode Forward Voltage	V _F	I _F = 30A T _J = 25°C, T _J = 125°C T _J = 150°C		1.65 1.65 1.70	2.00	V

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at T _J = 25°C						
Turn-on Delay Time	t _d (on)	V _{CC} =300V, I _C =30A, V _{GE} = -15v~15V, R _g =33Ω,Ls=60nH	-	37	-	ns
Rise Time	t _r		-	67	-	ns
Turn-on Energy	E _{on}		-	0.87	-	mJ
Turn-off Delay Time	t _d (off)		-	113	-	ns
Fall Time	t _f		-	16	-	ns
Turn-off Energy	E _{off}		-	0.26	-	mJ
Dynamic , at T _J = 125°C						
Turn-on Delay Time	t _d (on)	V _{CC} =300V, I _C =30A,, V _{GE} = -15v~15V, R _g =33Ω,Ls=60nH	-	40	-	ns
Rise Time	t _r		-	69	-	ns
Turn-on Energy	E _{on}		-	1.22	-	mJ
Turn-off Delay Time	t _d (off)		-	155	-	ns
Fall Time	t _f		-	18	-	ns
Turn-off Energy	E _{off}		-	0.38	-	mJ
Dynamic , at T _J = 150°C						
Turn-on Delay Time	t _d (on)	V _{CC} =300V, I _C =30A,, V _{GE} = -15v~15V, R _g =33Ω,Ls=60nH	-	41	-	ns
Rise Time	t _r		-	70	-	ns
Turn-on Energy	E _{on}		-	1.35	-	mJ
Turn-off Delay Time	t _d (off)		-	165	-	ns
Fall Time	t _f		-	20	-	ns
Turn-off Energy	E _{off}		-	0.45	-	mJ

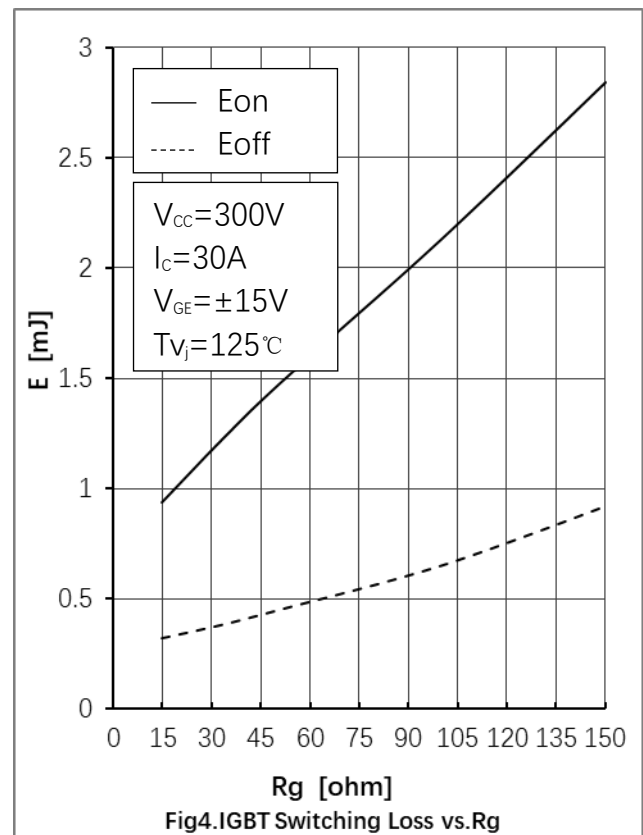
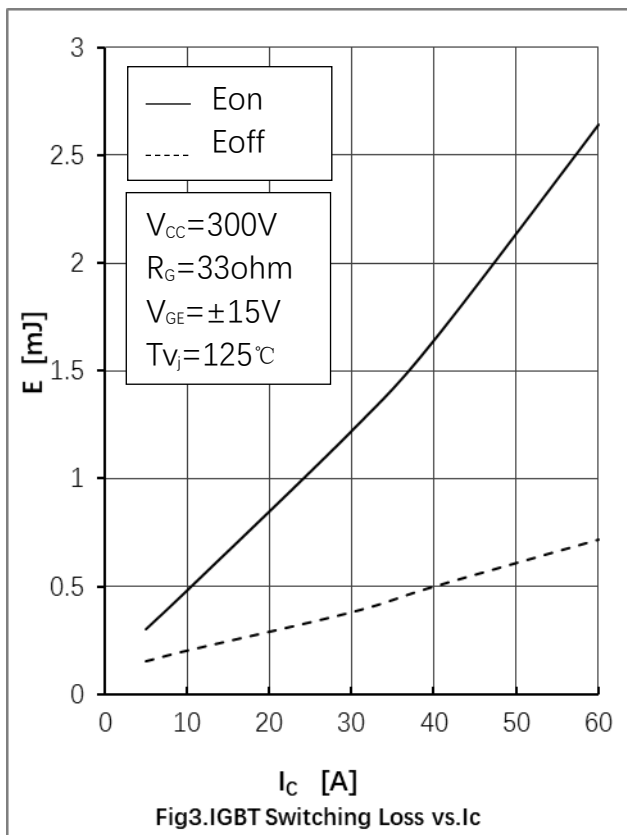
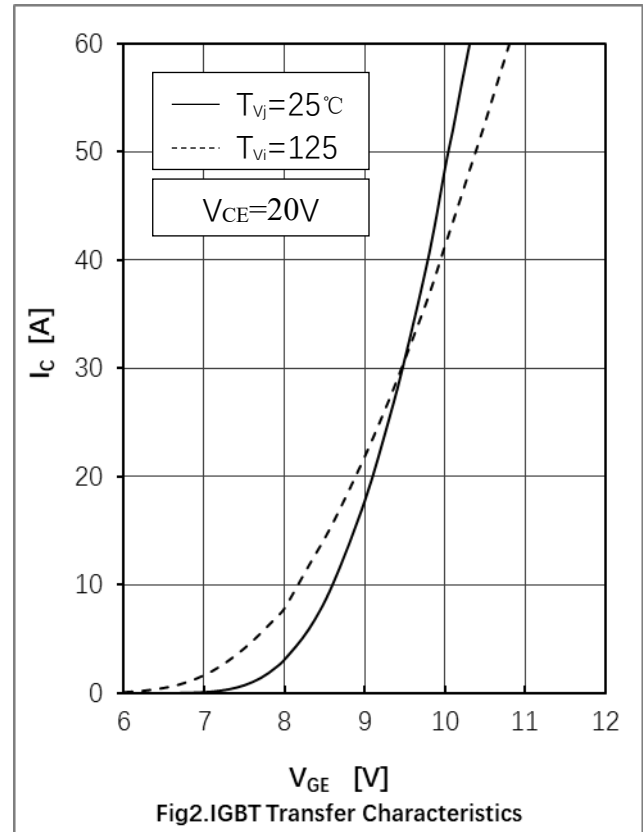
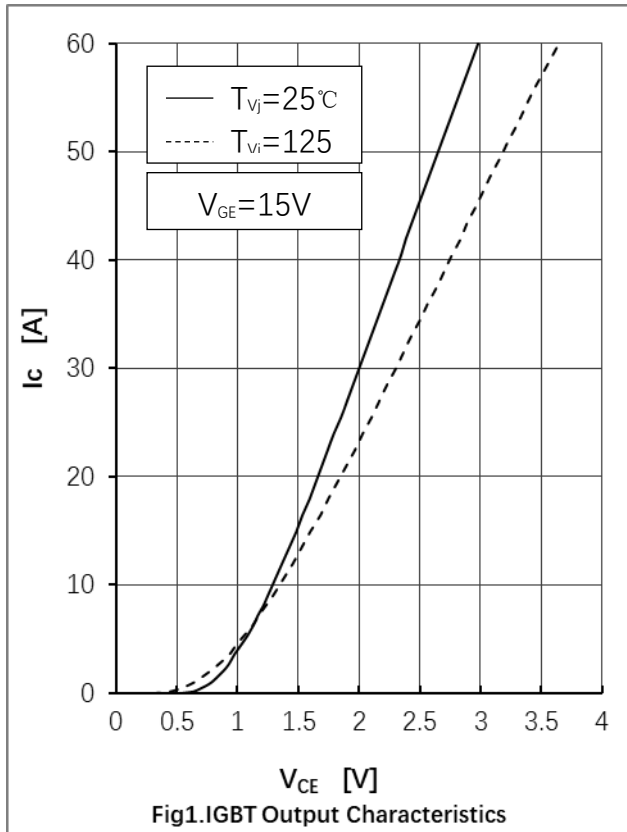


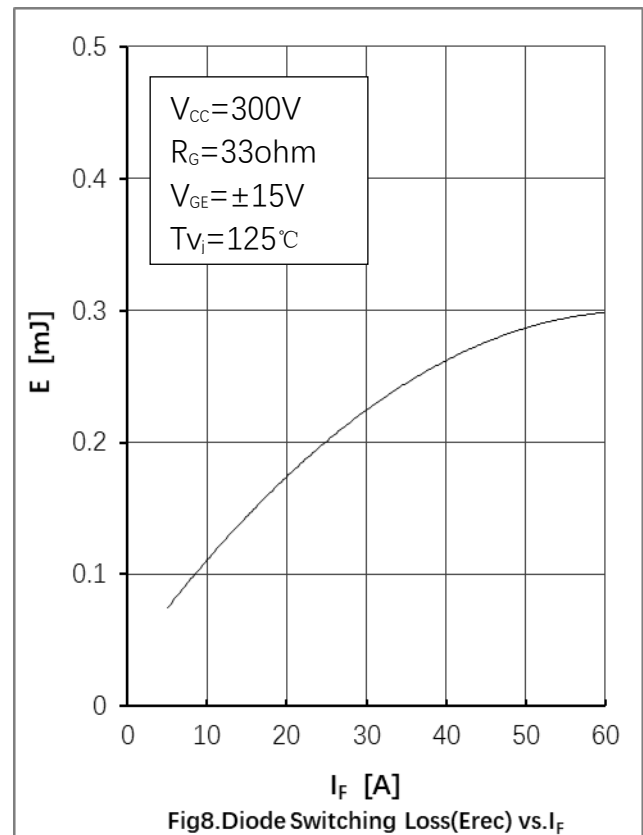
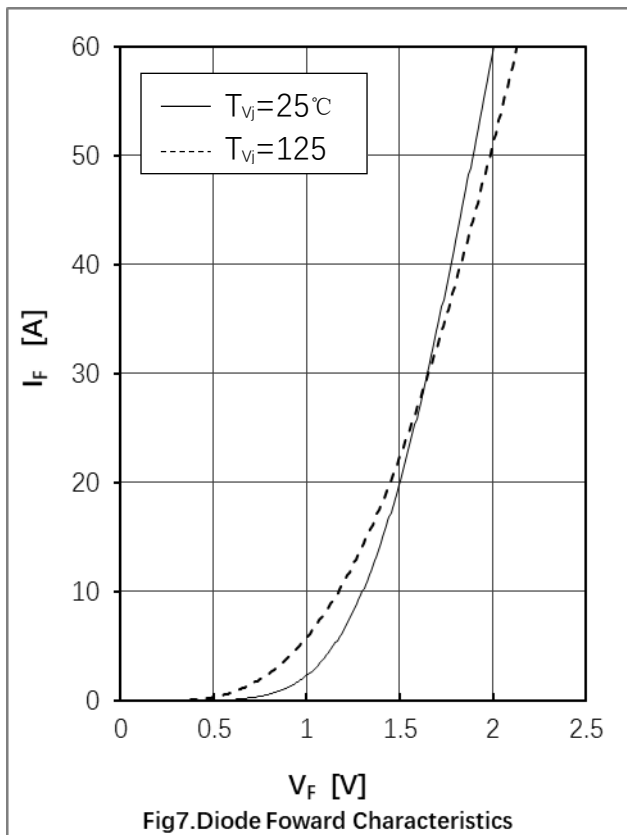
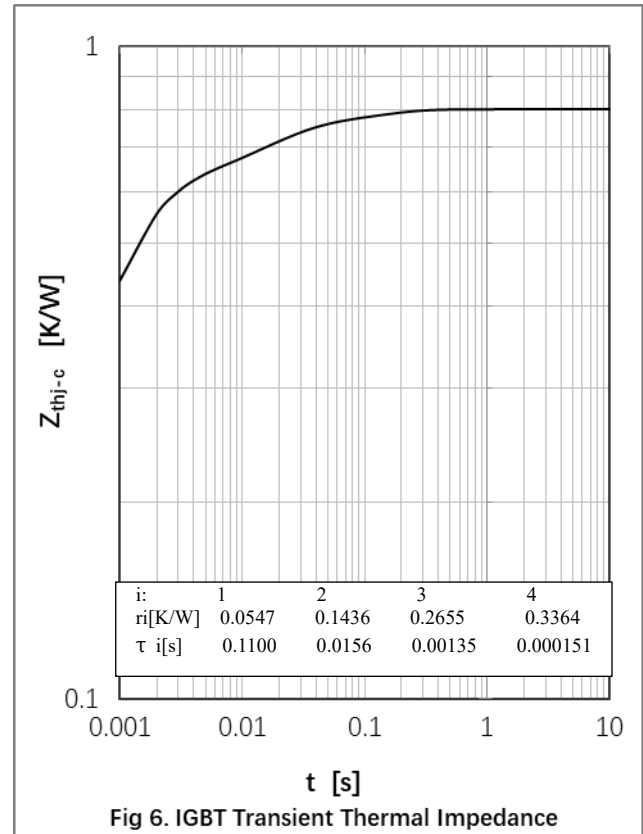
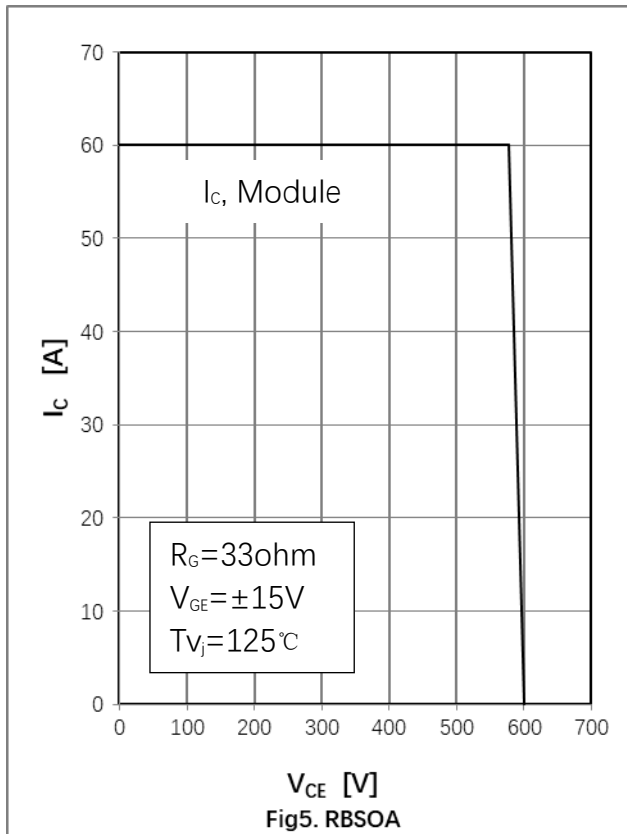
Electrical Characteristics of the Diode

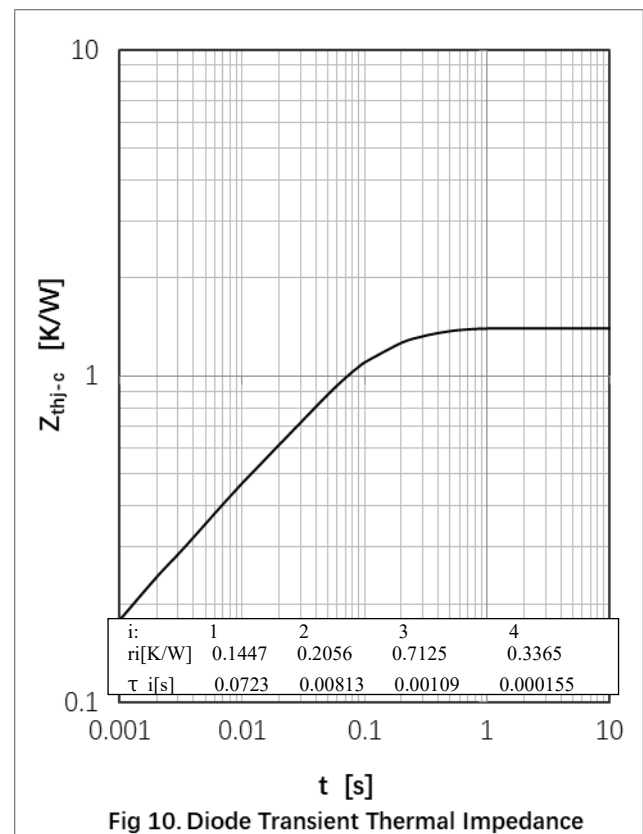
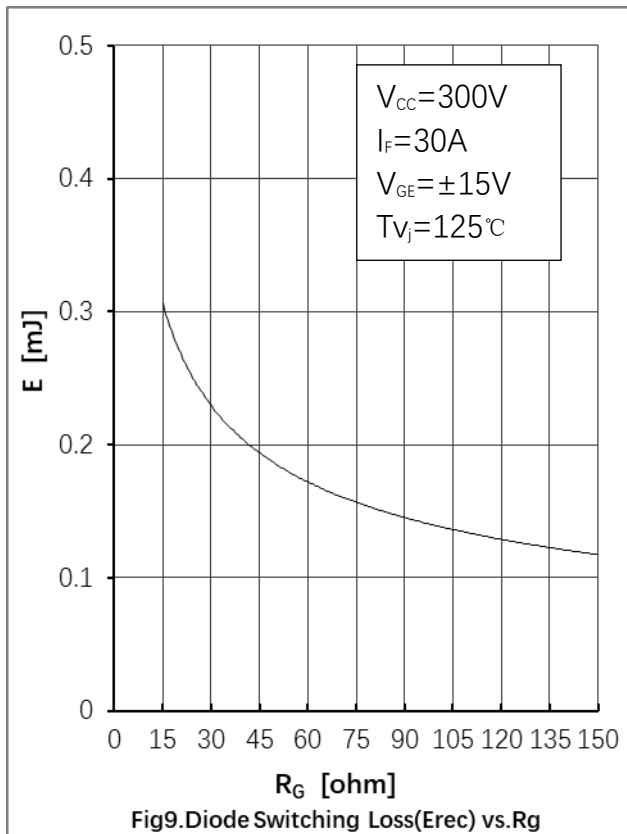
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at T _j = 25°C						
Diode Forward Voltage	V _{FM}	I _F = 30A	-	2.0	-	V
Reverse Recovery Current	I _{rr}	I _F =30A,V _R =300V di/dt= -300A/μs,	-	6.0	-	A
Reverse Recovery Charge	Q _{rr}		-	0.10	-	uC
Reverse Recovery Energy	E _{rec}		-	0.06		mJ
Dynamic , at T _j = 125°C						
Reverse Recovery Current	I _{rr}	I _F =30A,V _R =300V di/dt= -300A/μs,	-	10	-	A
Reverse Recovery Charge	Q _{rr}		-	0.22	-	nC
Reverse Recovery Energy	E _{rec}		-	0.13		mJ
Dynamic , at T _j = 150°C						
Reverse Recovery Current	I _{rr}	I _F =30A,V _R =300V di/dt= -300A/μs,	-	12	-	A
Reverse Recovery Charge	Q _{rr}		-	0.26	-	nC
Reverse Recovery Energy	E _{rec}		-	0.17		mJ

Thermal Resistance

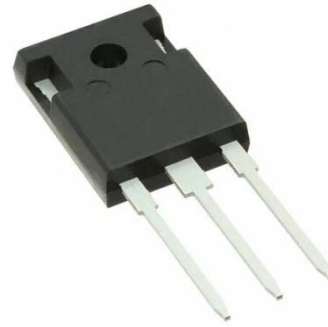
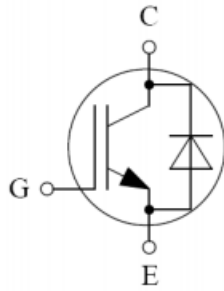
Parameter	Symbol	Max. Value	Unit
IGBT Thermal Resistance, Junction - Case	R _{θ(j-c)}	0.80	K/W
Diode Thermal Resistance, Junction - Case	R _{θ(j-c)}	1.4	K/W
Thermal Resistance, Junction - Ambient	R _{θ(j-a)}	40	K/W







Circuit Diagram



Package Outline Information

CASE: TO-247

